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Abstract of the Disclosure

The present invention relates to an integrated circuit having a sealed nitride layer. In one embodiment, a method of forming a sealing nitride layer overlaying a silicon oxide layer in a contact opening of an integrated circuit is disclosed. The method comprises, forming a second layer of nitride overlaying a first layer of nitride to form the sealing nitride layer. The second layer of nitride further overlays an exposed portion of a surface of a substrate in the contact opening and sidewalls of the contact opening. Using reactive ion etching (RIE etch) without a mask to remove a portion of the second nitride layer adjacent the surface of the substrate in the contact opening to expose a portion of the surface of the substrate in the contact opening without removing portions of the second nitride layer covering the sidewalls of the contact opening.

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